

Amendments the Claims

This listing of claims will replace all prior versions, and listings, of the claims:

1. (currently amended) A system-on-a-chip comprising:

a microprocessor;

a non-volatile imperfect semiconductor memory device;

a memory controller separate from the microprocessor and ~~transferring~~ configured to transfer data between the microprocessor and the non-volatile semiconductor imperfect memory device;

a buffer memory receiving plural data blocks from the microprocessor and sending the plural data blocks to the non-volatile semiconductor-based imperfect memory device; and

a buffer manager including (1) a hardware-implemented logic block managing transfer of the plural data blocks between the microprocessor and the non-volatile semiconductor-based imperfect memory device, and (2) a memory mapping block receiving from the non-volatile semiconductor-based imperfect memory device a memory map indicating reserved memory locations within the non-volatile semiconductor-based imperfect memory device,

wherein the buffer manager receives from the enables the microprocessor to access a first data block at a first location within the buffer memory while a second data block is concurrently written to the non-volatile semiconductor-based imperfect memory device from a second location within the buffer memory,

wherein the buffer manager receives plural set-up information blocks from the microprocessor,

wherein each of the set-up information blocks comprises information to transfer the plural data blocks between the microprocessor and the non-volatile semiconductor-based imperfect memory device.

2. (original) The system-on-a-chip of claim 1, further comprising:

a translator configured to translate logical block addresses to corresponding physical block addresses on the non-volatile imperfect semiconductor memory device during execution of a read or write command.

3. (original) The system-on-a-chip of claim 1, further comprising:

error correction of data transferred between the microprocessor and the non-volatile imperfect semiconductor memory device.

4. (original) The system-on-a-chip of claim 3, wherein the memory controller is configured to provide error correction.

5. (original) The system-on-a-chip of claim 1, wherein the non-volatile semiconductor-based imperfect memory device is an atomic resolution memory device.

6. (original) The system-on-a-chip of claim 1, wherein the non-volatile semiconductor-based imperfect memory device is a magnetic random access memory device.

7. (previously presented) The system-on-a-chip of claim 1, wherein the microprocessor reads and writes data directly to the non-volatile semiconductor-based imperfect memory device without a need for a separate memory controller chip or physical electrical interconnections.

8. (currently amended) A system-on-a-chip comprising:

a microprocessor;

a non-volatile semiconductor-based imperfect memory device; and

a memory controller separate from the microprocessor and receiving ~~configured to receive~~ from the microprocessor at least one data block having an associated logical block address, to translate the associated logical block address to a corresponding physical block address, to provide for the at least one data block an error correction code that is a function of the at least one data block, to send the at least one data block and error correction code to the non-volatile semiconductor-based imperfect memory device,

and to provide error detection and correction for the at least one data block based on the at least one data block and error correction code read from the non-volatile semiconductor-based imperfect memory device;

a buffer memory receiving plural data blocks, including the at least one data block, from the microprocessor and sending the plural data blocks to the non-volatile semiconductor-based imperfect memory device; and

a buffer manager enabling the microprocessor to access a first data block at a first location within the buffer memory while a second data block is concurrently written to the non-volatile semiconductor-based imperfect memory device from a second location within the buffer memory,

wherein the buffer manager receives plural set-up information blocks from the microprocessor,

wherein each of the set-up information blocks comprises information to transfer the plural data blocks between the microprocessor and the non-volatile semiconductor-based imperfect memory device.

9. (canceled)

10. (currently amended) The system-on-a-chip of claim ~~8-9~~, wherein the buffer memory is configured as a circular buffer.

11. (currently amended) The system-on-a-chip of claim ~~8-9~~, wherein the buffer memory comprises a number of bit positions wherein the number of bit positions is a multiple of a number of bit positions in the at least one data block.

12. (original) The system-on-a-chip of claim 11, wherein the number of buffer memory bit positions is a multiple of 512.

13. (canceled)

14. (currently amended) The system-on-a-chip of claim 8-13, wherein each set-up information blocks contains information comprising a number of data block to be transferred and their associated logical block addresses.

15. (currently amended) The system-on-a-chip of claim 8-13, wherein the plurality of set-up information blocks is stored in a plurality of set-up registers.

16. (original) The system-on-a-chip of claim 15, wherein the memory controller further comprises:

- a processor translator comprising:

- a hardware-implemented logic block configured to synchronize a transfer of the plurality of data blocks between the microprocessor and the buffer memory.

17. (original) The system-on-a-chip of claim 16, wherein the hardware-implemented logic block comprises:

- a plurality of buffers configured to synchronize transfer of the plurality data block between the microprocessor transferring data at a first bit-width and the buffer memory transferring data at a second bit-width.

18. (original) The system-on-a-chip of claim 16, wherein the hardware-implemented logic block comprises:

- a plurality of buffers configured to synchronize transfer of the plurality of data blocks between the microprocessor transferring data at a first data rate and the buffer memory transferring data at a second data rate.

19. (currently amended) The system-on-a-chip of claim 8-9, wherein the memory controller further comprises:

- a memory translator comprising:

- a hardware-implemented logic block configured to synchronize a transfer of the plurality of data blocks between the buffer memory and the non-volatile semiconductor-based imperfect memory device.

20. (original) The system-on-a-chip of claim 19, wherein the hardware-implemented logic block comprises:

a plurality of buffers configured to synchronize transfer of the plurality of data blocks between the microprocessor transferring data at a first bit-width and the buffer memory transferring data at a second bit-width.

21. (original) The system-on-a-chip of claim 19, wherein the hardware-implemented logic block comprises:

a plurality of buffers configured to synchronize transfer of the plurality of data blocks between the microprocessor transferring data at a first data rate and the buffer memory transferring data at a second data rate.

22. (currently amended) The system-on-a-chip of claim 8-9, wherein the memory controller further comprises:

a memory interface configured to receive from the buffer manager the physical block address for the at least one data block, to provide the error correction code for the at least one data block, to write/read the at least one data block and associated error correction code to/from the non-volatile semiconductor-based imperfect memory device, and to provide the error correction/detection for the at least one data block using the at least one data block and associated error correction code read from the non-volatile semiconductor-based imperfect memory device.

23. (original) The system-on-a-chip of claim 22, wherein the memory interface comprises a hardware implemented logic block.

24. (currently amended) A mobile electronic device comprising:

a system-on-a-chip comprising:

a microprocessor;~~and~~

a non-volatile semiconductor-based imperfect memory device;~~and~~

a memory controller separate from the microprocessor and configured to receive from the microprocessor at least one data block having an associated logical block address, to translate the associated logical block address to a corresponding physical block address, to provide for the at least one data block an error correction code (ECC) that is a function of the at least one data block, and to send the at least one data block and error correction code to the non-volatile semiconductor-based imperfect memory device;

a buffer memory receiving plural data blocks from the microprocessor and sending the plural data blocks to the non-volatile semiconductor-based imperfect memory device; and

a buffer manager including (1) a hardware-implemented logic block managing transfer of the plural data blocks between the microprocessor and the non-volatile semiconductor-based imperfect memory device, and (2) a memory mapping block receiving from the non-volatile semiconductor-based imperfect memory device a memory map indicating reserved memory locations within the non-volatile semiconductor-based imperfect memory device,

wherein the buffer manager enables the microprocessor to access a first data block at a first location within the buffer memory while a second data block is concurrently written to the non-volatile semiconductor-based imperfect memory device from a second location within the buffer memory,

wherein the buffer manager receives plural set-up information blocks from the microprocessor,

wherein each of the set-up information blocks comprises information to transfer the plural data blocks between the microprocessor and the non-volatile semiconductor-based imperfect memory device.

25. (previously presented) The mobile electronic device of claim 24, wherein the non-volatile semiconductor-based imperfect memory device is an ultra-high density atomic resolution memory device.

26. (previously presented) The mobile electronic device of claim 24, wherein the non-volatile semiconductor-based imperfect memory device is a magnetic random access memory device.

27. (canceled)